

Ryuji Katayama

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

87
papers

571
citations

12
h-index

17
g-index

94
ext. papers

626
ext. citations

1.6
avg, IF

2.98
L-index

#	Paper	IF	Citations
87	Improvement of surface morphology of nitrogen-polar GaN by introducing indium surfactant during MOVPE growth. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 085501	1.4	16
86	Enhancement of surface migration by Mg doping in the metalorganic vapor phase epitaxy of N-polar $\{000\bar{1}\}$ GaN/sapphire. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 05FL05	1.4	12
85	Effect of c-plane sapphire substrate miscut angle on indium content of MOVPE-grown N-polar InGaN. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 05FL07	1.4	6
84	Molecular beam epitaxy of ErGaAs alloys on GaAs (0 0 1) substrates. <i>Journal of Crystal Growth</i> , 2013 , 378, 85-87	1.6	1
83	Investigation of indium incorporation into InGaN by nitridation of sapphire substrate in MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 417-420		3
82	RF-MBE growth of cubic AlN on MgO (001) substrates via 2-step c-GaN buffer layer. <i>Journal of Crystal Growth</i> , 2013 , 378, 307-309	1.6	4
81	Optical properties of InN films grown by pressurized-reactor metalorganic vapor phase epitaxy. <i>Thin Solid Films</i> , 2013 , 536, 152-155	2.2	9
80	AlGaIn/GaN MIS-gate HEMTs with SiCN gate stacks. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 790-793		1
79	Key Factors for Metal Organic Chemical Vapor Deposition of InGaIn Films with High InN Molar Fraction. <i>Applied Mechanics and Materials</i> , 2013 , 341-342, 204-207	0.3	
78	A Novel Material for Laser Diodes of Optical Fiber Communication. <i>Advanced Materials Research</i> , 2013 , 760-762, 45-49	0.5	
77	Relationship between residual carrier density and phase purity in InN grown by pressurized-reactor MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 681-684		3
76	Phase diagram on phase purity of InN grown pressurized-reactor MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 654-657		10
75	Single Photon Generation from Nitrogen Atomic-Layer Doped Gallium Arsenide. <i>Materials Science Forum</i> , 2012 , 706-709, 2916-2921	0.4	2
74	Effect of Nitridation on Indium-Composition of InGaIn Films. <i>Key Engineering Materials</i> , 2012 , 508, 193-198		4
73	Optical properties of the periodic polarity-inverted GaN waveguides 2012 ,		4
72	Scanning tunneling microscope-based local electroluminescence spectroscopy of p-AlGaAs/i-GaAs/n-AlGaAs double heterostructure. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 021802	1.3	1
71	Effect of Phase Purity on Dislocation Density of Pressurized-Reactor Metalorganic Vapor Phase Epitaxy Grown InN. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 04DH02	1.4	5

70	Tilted Domain and Indium Content of InGa _N Layer on $\sqrt{m}\sqrt{m}$ -Plane GaN Substrate Grown by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 04DH01	1.4	3
69	Biexciton Luminescence from Individual Isoelectronic Traps in Nitrogen δ -Doped GaAs. <i>Applied Physics Express</i> , 2012 , 5, 111201	2.4	8
68	Effect of growth temperature on structure properties of InN grown by pressurized-reactor metalorganic vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 482-484		10
67	Carrier-concentration dependent photoluminescence of InAsN films grown by RF-MBE. <i>Journal of Crystal Growth</i> , 2011 , 323, 26-29	1.6	4
66	Development of Novel System Combining Scanning Tunneling Microscope-Based Cathodoluminescence and Electroluminescence Nanospectroscopies. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 08LB18	1.4	
65	Paving the way to high-quality indium nitride: the effects of pressurized reactor 2011 ,		5
64	Lattice-Latching Effect in Metalorganic Vapor Phase Epitaxy Growth of InGaAsN Film Lattice-Matched to Bulk InGaAs Substrate. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 040202	1.4	2
63	Photoluminescence study of type-II InGaPN/GaAs quantum wells. <i>Journal of Nanoscience and Nanotechnology</i> , 2010 , 10, 7154-7	1.3	
62	Band alignment of lattice-matched InGaPN/GaAs and GaAs/InGaPN quantum wells grown by MOVPE. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010 , 42, 1176-1179	3	1
61	Photoluminescence from single isoelectronic traps in nitrogen delta-doped GaAs grown on GaAs(111)A. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010 , 42, 2529-2531	3	12
60	MOVPE growth and optical characterization of InGaAsN T-shaped quantum wires lattice-matched to GaAs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1418-1420	1.6	3
59	MOVPE growth of high optical quality InGaPN layers on GaAs (001) substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 2079-2081		1
58	Lateral patterning of GaN polarity using wet etching process. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 1922-1924		3
57	Scanning tunneling microscope cathodoluminescence measurement of the GaAs/AlGaAs heterostructure. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 1874		7
56	Metastable cubic InN layers on GaAs (001) substrates grown by MBE: Growth condition and crystal structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S376-S380		5
55	MOVPE growth of InN films using 1,1-dimethylhydrazine as a nitrogen precursor. <i>Journal of Crystal Growth</i> , 2009 , 311, 2802-2805	1.6	4
54	Band gap energy fluctuations in InGa _N films grown by RF-MBE with changing nitrogen supply rate investigated by a piezoelectric photothermal spectroscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 499-502		1
53	RF-MBE growth of cubic InN films on YSZ(001) vicinal substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1712-1714		2

52	MOVPE growth and photoluminescence properties of InAsN QDs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1715-1718		1
51	Electrical conduction in cubic GaN films grown on GaAs(001) by RF-MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1805-1807		3
50	Incorporation of N in high N-content GaAsN films investigated by Raman scattering. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 2923-2925		
49	Twin photoluminescence peaks from single isoelectronic traps in nitrogen doped GaAs. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008 , 40, 2110-2112	3	16
48	Characterization of MOVPE Grown GaAs _{1-x} N _x /GaAs Multiple Quantum Wells Emitting Around 1.3- μ m-Wavelength Region 2007 ,		1
47	Substrate-surface orientation dependence of N content in MOVPE growth of GaAsN films on GaAs. <i>Journal of Crystal Growth</i> , 2007 , 298, 135-139	1.6	4
46	Correlation between Raman intensity of the N-related local vibrational mode and N content in GaAsN strained layers grown by MOVPE. <i>Journal of Crystal Growth</i> , 2007 , 298, 107-110	1.6	10
45	Structural investigation of InGaAsN films grown on pseudo-lattice-matched InGaAs substrates by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2007 , 298, 111-115	1.6	7
44	Micro-photoluminescence study of nitrogen delta-doped GaAs grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2007 , 298, 73-75	1.6	11
43	MOVPE and characterization of InAsN/GaAs multiple quantum wells. <i>Journal of Crystal Growth</i> , 2007 , 298, 544-547	1.6	11
42	Growth and post-growth rapid thermal annealing of InGaPN on GaP grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2007 , 298, 150-153	1.6	2
41	Post-growth thermal annealing of high N-content GaAsN by MOVPE and its effect on strain relaxation. <i>Journal of Crystal Growth</i> , 2007 , 298, 140-144	1.6	7
40	Photoluminescence and photoluminescence-excitation spectroscopy of InGaPN/GaP lattice-matched single quantum well structures grown by MOVPE. <i>Journal of Crystal Growth</i> , 2007 , 298, 531-535	1.6	2
39	MOVPE growth and optical characterization of GaPN films using tertiarybutylphosphine (TBP) and 1,1-dimethylhydrazine (DMHy). <i>Journal of Crystal Growth</i> , 2007 , 298, 103-106	1.6	3
38	RFMBE growth and structural characterization of cubic InN films on yttria-stabilized zirconia (001) substrates. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 508-512	1.6	10
37	Growth of In-rich InGaN films on sapphire via GaN layer by RF-MBE. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 473-477	1.6	18
36	Fabrication of lateral lattice-polarity-inverted GaN heterostructure. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 447-451	1.6	12
35	Nitrogen supply rate dependence of InGaN growth properties, by RF-MBE. <i>Journal of Crystal Growth</i> , 2007 , 305, 12-18	1.6	28

34	Structural and optical characterization of high In content cubic InGaN on GaAs(001) substrates by RF-MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 2437-2440		2
33	InAsN quantum dots grown on GaAs(001) substrates by MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 2387-2390		1
32	Shutterless nitrogen flux modulation using a dual-mode rf-plasma operation during RF-MBE growth of GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 277-281	1.6	1
31	Structural transition control of laterally overgrown c-GaN and h-GaN on stripe-patterned GaAs (001) substrates by MOVPE. <i>Physica Status Solidi (B): Basic Research</i> , 2007 , 244, 1769-1774	1.3	11
30	Surface photovoltage spectroscopy characterization of InGaPN alloys grown on GaP substrates. <i>Journal of Physics Condensed Matter</i> , 2007 , 19, 096009	1.8	3
29	Modulation spectroscopic investigation on lattice polarity of gallium nitride. <i>Applied Physics Letters</i> , 2007 , 91, 061917	3.4	10
28	Piezoelectric Photothermal and Photoreflectance Spectra of In _x Ga _{1-x} N Grown by Radio-Frequency Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 4601-4603	1.4	12
27	Complementary analyses on the local polarity in lateral polarity-inverted GaN heterostructure on sapphire (0001) substrate. <i>Applied Physics Letters</i> , 2006 , 89, 231910	3.4	21
26	High-nitrogen-content InGaAsN films on GaAs grown by metalorganic vapor phase epitaxy with TBAs and DMHy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 1612-1617	1.6	7
25	MOVPE growth and optical characterization of GaAsN films with higher nitrogen concentrations. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 1641-1644	1.6	11
24	MOVPE growth of InAsN films on GaAs(001) substrates with an InAs buffer layer. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1411-1415	1.3	10
23	RF-MBE growth and structural characterization of cubic InN films on GaAs. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1451-1455	1.3	16
22	Growth and optical characterization of InAsN quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1657-1660	1.3	8
21	Buffer design for nitrogen polarity GaN on sapphire by RF-MBE and application to the nanostructure formation using KOH etching. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006 , 32, 245-248	3	13
20	MOVPE growth and optical investigations of InGaPN alloys. <i>Journal of Crystal Growth</i> , 2005 , 275, e1017-e1021	1.6	5
19	Growth mechanism and structural characterization of hexagonal GaN films grown on cubic GaN (1 1 1)/GaAs (1 1 1)B substrates by MOVPE. <i>Journal of Crystal Growth</i> , 2005 , 275, e1023-e1027	1.6	2
18	Excitation power dependent photoluminescence of In _{0.7} Ga _{0.3} As _{1-x} N _x quantum dots grown on GaAs (0 0 1). <i>Journal of Crystal Growth</i> , 2005 , 278, 244-248	1.6	6
17	Fabrication of cubic and hexagonal GaN micro-crystals on GaAs(0 0 1) substrates with relatively thin low-temperature GaN buffer layer. <i>Journal of Crystal Growth</i> , 2005 , 278, 431-436	1.6	2

16	Growth and characterization of InAsN alloy films and quantum wells. <i>Journal of Crystal Growth</i> , 2005 , 278, 254-258	1.6	32
15	Optical characterization of InAsN single quantum wells grown by RF-MBE. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 2791-2794	1.3	9
14	Highly luminescent cubic GaN microcrystals grown on GaAs(001) substrates by RF-MBE. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 2739-2743	1.3	1
13	Built-in electric field at cubic GaN/GaAs(001) heterointerfaces investigated by phase-selected photoreflectance excitation. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 2749-2753	1.3	2
12	MBE growth and photoreflectance study of GaAsN alloy films grown on GaAs (0 0 1). <i>Journal of Crystal Growth</i> , 2003 , 251, 427-431	1.6	19
11	RF-MBE growth of InAsN layers on GaAs (001) substrates using a thick InAs buffer layer. <i>Journal of Crystal Growth</i> , 2003 , 251, 422-426	1.6	11
10	Characterization of MOVPE-grown GaN layers on GaAs (111)B with a cubic-GaN (111) epitaxial intermediate layer. <i>Physica Status Solidi (B): Basic Research</i> , 2003 , 240, 305-309	1.3	2
9	Electrically biased photoreflectance study of cubic GaN/GaAs(001) heterointerface. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2597-2601		4
8	Microstructures, defects, and localization luminescence in InGaAsN alloy films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2778-2781		3
7	Hall effect measurement of InAsN alloy films grown directly on GaAs(001) substrates by RF-MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2765-2768		21
6	MOVPE growth and characterization of high-N content InGaPN alloy lattice-matched to GaP. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2773-2777		9
5	Physical Mechanisms of Photoluminescence of InGaAs(N) Alloy Films Grown by MOVPE. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 234, 782-786	1.3	2
4	Reduction of Planar Defect Density in Laterally Overgrown Cubic-GaN on Patterned GaAs(001) Substrates by MOVPE. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 234, 840-844	1.3	8
3	Photoconductivity and Electoreflectance Study of Cubic GaN/GaAs(001) Heterostructures by Optical-Biasing Technique. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 234, 877-881	1.3	2
2	Cubic GaN Films on GaAs (001) Substrates without Deep-Level Luminescence Grown by Metalorganic Vapor Phase Epitaxy. <i>Physica Status Solidi A</i> , 2000 , 180, 15-19		4
1	Substrate Misorientation Dependence of the Hexagonal Phase Inclusion in Cubic GaN Films Grown by Metalorganic Vapor Phase Epitaxy. <i>Physica Status Solidi A</i> , 1999 , 176, 513-517		7